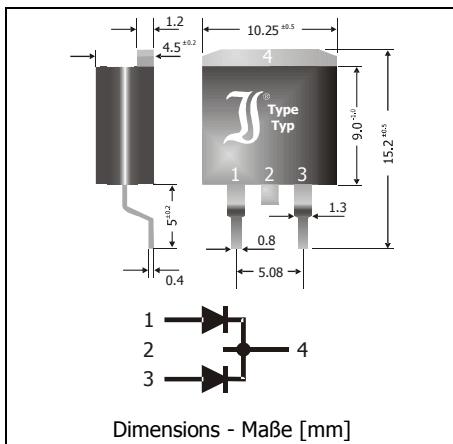


## SK3020CD2 ... SK30100CD2

### Surface Mount Schottky Rectifier Diodes— Common Cathode Schottky-Gleichrichterdioden für die Oberflächenmontage – Gemeinsame Kathode

Version 2012-01-16



Nominal Current Nennstrom	30 A
Repetitive peak reverse voltage Periodische Spitzensperrspannung	20...100 V
Plastic case Kunststoffgehäuse	TO-263 D2PAK
Weight approx. – Gewicht ca.	1.6 g
Plastic material has UL classification 94V-0 Gehäusematerial UL94V-0 klassifiziert	 Green Molding Halogen-Free <sup>1</sup>
Standard packaging in tubes Standard Lieferform in Stangen	

### Maximum ratings and Characteristics

### Grenz- und Kennwerte

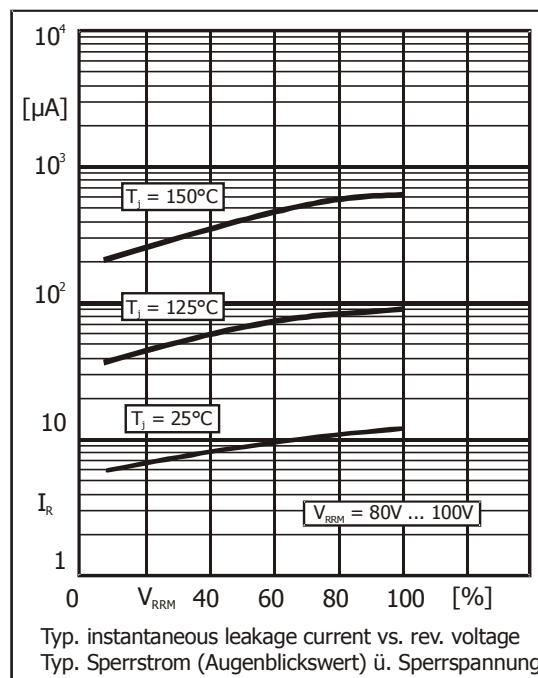
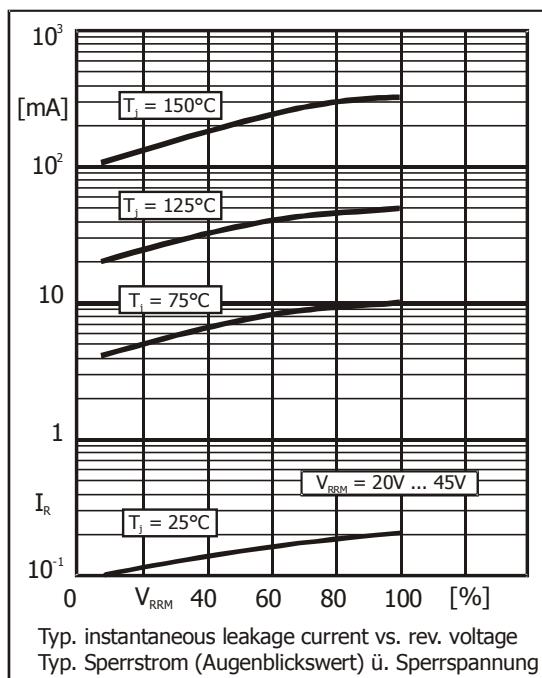
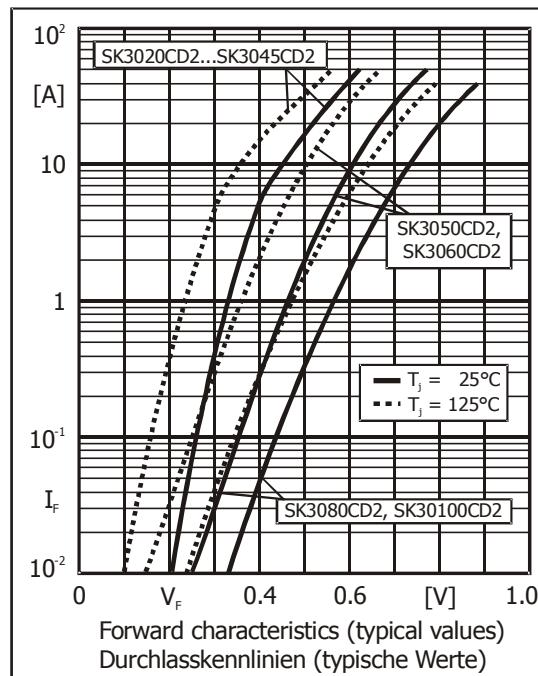
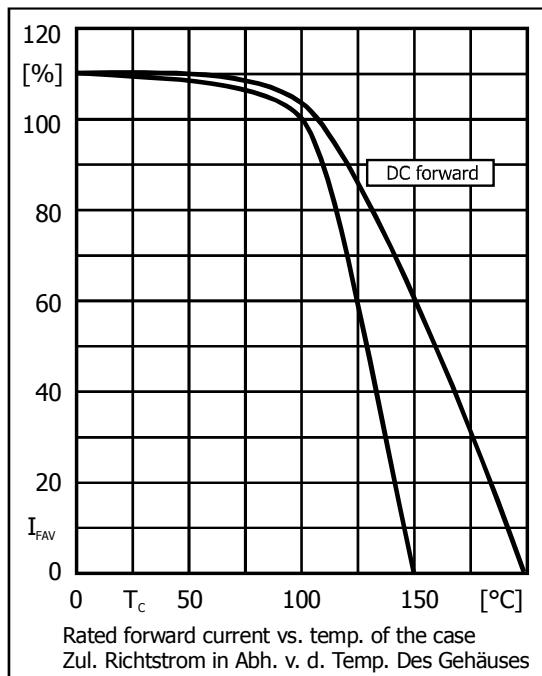
Type Typ	Repetitive peak reverse voltage Periodische Spitzensperrspannung $V_{RRM}$ [V]	Surge peak reverse voltage Stoßspitzensperrspannung $V_{RSM}$ [V]	Forward Voltage Durchlass-Spannung $V_F$ [V] <sup>2)</sup> <sup>3)</sup>	$I_F = 5$ A	$I_F = 15$ A
SK3020CD2	20	20	< 0.49	< 0.55	
SK3030CD2	30	30	< 0.49	< 0.55	
SK3040CD2	40	40	< 0.49	< 0.55	
SK3045CD2	45	45	< 0.49	< 0.55	
SK3050CD2	50	50	< 0.63	< 0.70	
SK3060CD2	60	60	< 0.63	< 0.70	
SK3080CD2	80	80	< 0.77	< 0.85	
SK30100CD2	100	100	< 0.77	< 0.85	

Max. average forward rectified current, R-load Dauergrenzstrom in Einwegschaltung mit R-Last	$T_C = 100^\circ\text{C}$	$I_{FAV}$ $I_{FAV}$	15 A <sup>3)</sup> 30 A <sup>4)</sup>	
Repetitive peak forward current – Periodischer Spitzenstrom $f > 15$ Hz		$I_{FRM}$	55 A <sup>3)</sup>	
Peak forward surge current 50/60 Hz half sine-wave Stoßstrom für eine 50/60 Hz Sinus-Halbwelle	$SK3020CD2\dots$ $SK3060CD2$	$T_A = 25^\circ\text{C}$	$I_{FSM}$	280/320 A <sup>3)</sup>
	$SK3080CD2\dots$ $SK30100CD2$	$T_A = 25^\circ\text{C}$	$I_{FSM}$	240/270 A <sup>3)</sup>
Rating for fusing, $t < 10$ ms – Grenzlastintegral, $t < 10$ ms	$T_A = 25^\circ\text{C}$	$i^2t$	390 A <sup>2</sup> s <sup>3)</sup>	
Junction temperature – Sperrsichttemperatur in DC forward mode – bei Gleichstrom-Durchlassbetrieb		$T_j$ $T_j$	-50...+150°C $\leq 200^\circ\text{C}$	
Storage temperature – Lagerungstemperatur		$T_s$	-50...+175°C	

<sup>1</sup> From 2H/2012 – Ab 2H/2012<sup>2</sup>  $T_j = 25^\circ\text{C}$ <sup>3</sup> Per diode; data for SK3050CD2...SK3060CD2 preliminary – Pro Diode; Daten für SK3050CD2...SK3060CD2 vorläufig<sup>4</sup> Per device (parallel operation) – Pro Bauteil (Parallelbetrieb)

**Characteristics**

Leakage current Sperrstrom	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$	$I_R$	< 500 $\mu\text{A}$ <sup>1)</sup>
Thermal resistance junction to case Wärmewiderstand Sperrsicht - Gehäuse			$R_{thC}$	< 1.5 K/W <sup>2)</sup>


<sup>1</sup> Per diode – Pro Diode

<sup>2</sup> Per device (parallel operation) – Pro Bauteil (Parallelbetrieb)